

30V P-Channel MOSFET

Product Summary

V(BR)DSS	R _{DS(on)MAX}	lo
	65mΩ@-10V	
-30V	75mΩ@-4.5V	-4.2A
	90mΩ@-2.5V	

Feature

- TrenchFET Power MOSFET
- Exceptional on-resistance and maximum DC current capability

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:



ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

SOT-23
Schematic diagram

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current	lD	-4.2	A
Power Dissipation	PD	0.35	W
Thermal Resistance from Junction to Ambient	Reja	357	°C /W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

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RS3401E

MOSFET ELECTRICAL CHARACT	ERISTICS(Ta=25°C	unless otherwise noted)

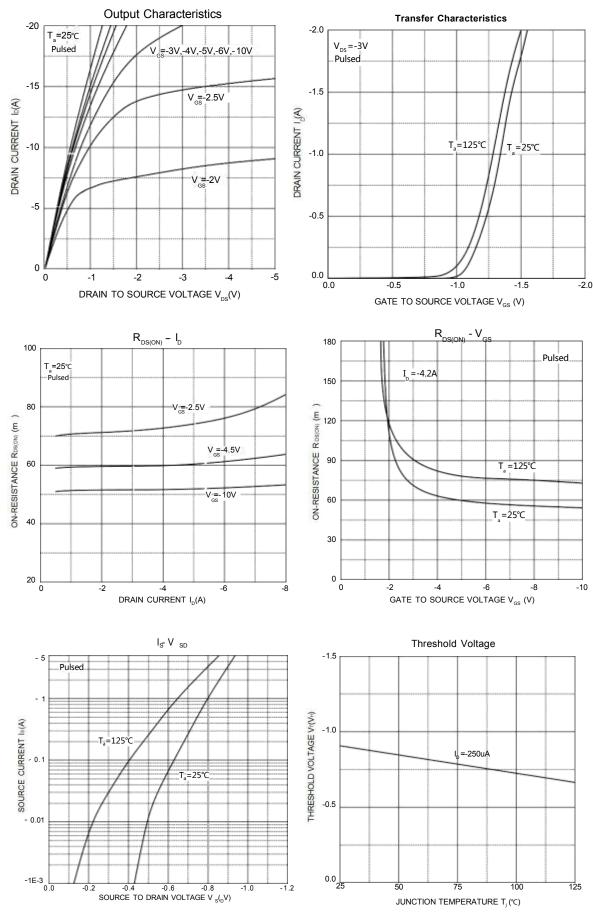
Parameter	Symbol	Test Condition	Min	Туре	Max	Unit	
Static Characteristics							
Drain-source breakdown voltage	V(BR)DSS	V _{GS} = 0V, I _D =-250µA	-30			V	
Zero gate voltage drain current	I _{DSS}	V _{DS} =-24V,V _{GS} = 0V			-1	μA	
Gate-body leakage current	Igss	Vgs =±12V, V _{DS} = 0V			±100	nA	
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250µA	-0.7	-0.9	-1.3	V	
		V _{GS} =-10V, I _D =-4.2A		50	65		
Drain-source on-resistance ⁽¹⁾	R _{DS(on)}	V _{GS} =-4.5V, I _D =-4A		60	75	mΩ	
		Vgs =-2.5V, ID =-1A		70	90		
Forward tranconductance ⁽¹⁾	g fs	VDS =-5V, ID =-4.2A		10		S	
Dynamic characteristics ⁽²⁾	i		i				
Input Capacitance	Ciss			954			
Output Capacitance	Coss	V _{DS} =-15V,V _{GS} =0V,f =1MHz		115		pF	
Reverse Transfer Capacitance	Crss			77			
Switching characteristics ⁽²⁾	· · ·						
Turn-on delay time	t _{d(on)}				6.3		
Turn-on rise time	tr	Vgs=-10V,Vds=-15V,			3.2		
Turn-off delay time	t _{d(off)}	RL=3.6Ω,R _{GEN} =6Ω			38.2	ns	
Turn-off fall time	t _f	-			12	1	
Source-Drain Diode characteristics	; ;	·					
Diode forward current	ls				-2	А	
Diode pulsed forward current	I _{SM}				-25	А	
Diode Forward voltage(1)	V _{DS}	V _{GS} =0V, I _S =-4.2A			-1.2	V	

Notes:

1. Pulse test; pulse width≤300µs, duty cycle≤2%.

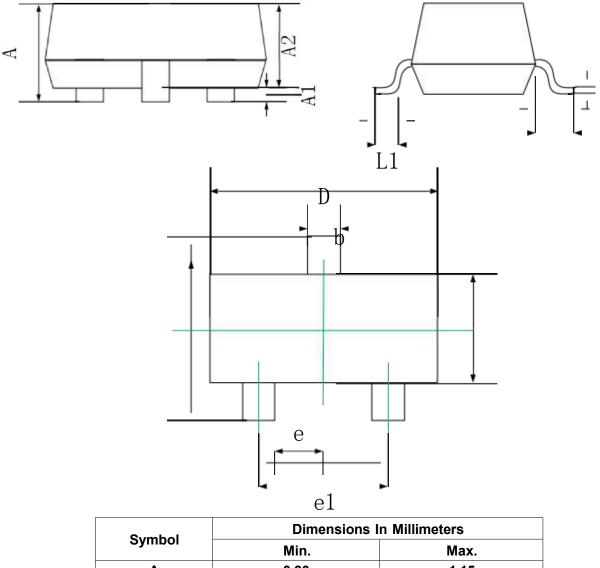
2. Guaranteed by design, not subject to production testing.

Typical Electrical and Thermal Characteristics





SOT-23 Package Information



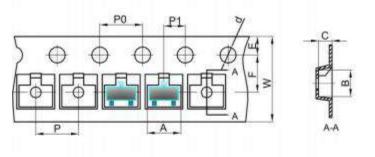
Symbol	Dimensions I	n Millimeters
Symbol	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
С	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
е	0.95	REF.
e1	1.80	2.00
L	0.55	REF.
L1	0.30	0.50



SOT-23 Tape and Reel

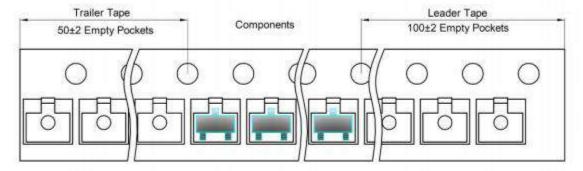
SOT-23 Tape and reel

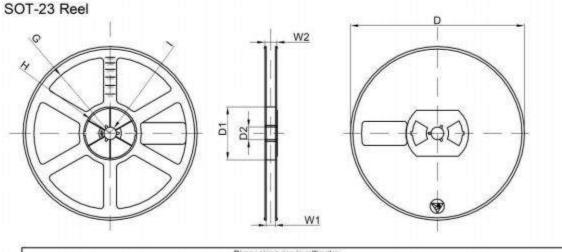
SOT-23 Embossed Carrier Tape



Dimensions are in millimeter										
Pkg type	A	В	С	d	E	F	PO	Р	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer





			Dimensio	ons are in millime	ter			
Reel Option	D	D1	D2	G	н	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	



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